

SEMICONDUCTOR DEVICE, LIQUID CRYSTAL DISPLAY DEVICE, EL DISPLAY DEVICE, SEMICONDUCTOR FILM PRODUCING METHOD, AND SEMICONDUCTOR DEVICE PRODUCING METHOD

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Inventor: NISHITANI HIKARU (JP); YAMAMOTO MAKOTO (JP); TAKETOMI YOSHINAO (US)

Applicant: MATSUSHITA ELECTRIC IND CO LTD (JP); NISHITANI HIKARU (JP); YAMAMOTO MAKOTO (JP); TAKETOMI YOSHINAO (US)

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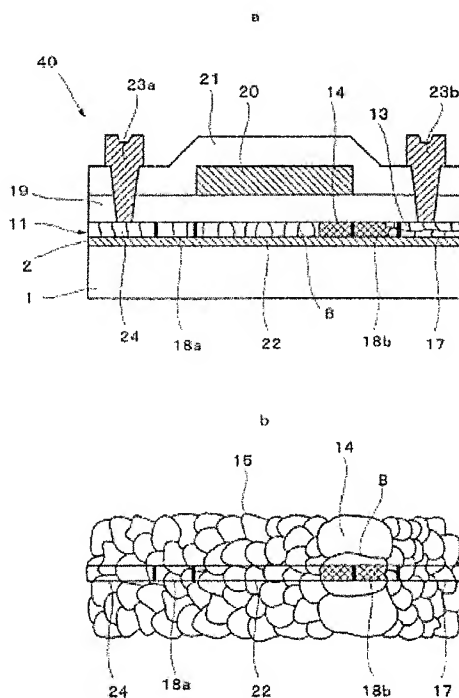
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Abstract of WO0209192

A semiconductor device characterized by comprising a thin film transistor (40) having a multicrystal semiconductor layer (11), the semiconductor layer (11) containing a channel region (22), high-concentration impurity regions (24, 17) positioned on opposite sides of the channel region (22), and low-concentration impurity regions (18a, 18b) positioned between the channel region (22) and the high-concentration impurity regions (24, 17) and having a lower impurity concentration than that of the high-concentration impurity regions (24, 17), wherein the particle size of crystals (14) at least part of which are present in the low-concentration impurity region (18b) is greater than that of other crystals (15).



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